

IN THE CLAIMS:

Please amend claim 11 as follows:

--11. (Amended) A method for removing a deposited film inside a chamber which comprises:

providing a hot element in the chamber, said hot element disposed away from the deposited film, the hot element having at least a surface which comprises platinum;

exhausting said chamber;

heating the hot element to 400° C. or higher;

supplying a cleaning gas into the chamber;

contacting the cleaning gas with the heated hot element to decompose and/or activate the cleaning gas and generate an activated species therefrom;

allowing the activated species to convert the deposited film into a gaseous substance;

and

removing the gaseous substance from the chamber.--

Please add claims 21 and 32 as follows:

--21. A method for removing a deposited film inside a chamber, said method comprising:

providing a hot element outside said chamber, said hot element having at least a surface composed of platinum;

exhausting said chamber;

heating said hot element;

contacting a cleaning gas with said hot element and activating said cleaning gas;

thereafter introducing said activated cleaning gas into said chamber and contacting a deposited film inside said chamber with said activated cleaning gas, whereby said activated gas converts the deposited film into a gaseous substance; and

removing said gaseous substance from the chamber--

--22. The method according to claim 21, wherein said chamber comprises a CVD apparatus and the method further comprises:

heating the hot element;
supplying a material gas to the chamber;
contacting the material gas with the hot element to cause decomposition and/or
activation of the material gas by said hot element; and
forming the deposited film which comprises at least one element from said material
gas on a substrate.--

--23. The method according to claim 21, wherein at least a part of a surface of an
inner structure of said chamber is covered with platinum.--

--24. The method according to claim 22, wherein at least a part of the surface of an
inner structure of said chamber is covered with platinum.- -

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und
--25. The method according to claim 21, wherein said cleaning gas is a gas containing
at least one of fluorine (F₂), chlorine (Cl₂), nitrogen trifluoride (NF₃), carbon tetrafluoride
(CF₄), hexafluoroethane (C₂F₆), octafluoropropane (C₃F₈), carbon tetrachloride (CCl₄),
pentafluorochloroethane (C₂ClF₅), trifluorochlorine (ClF₃), trifluorochloromethane (CClF₃),
and sulfur hexafluoride (SF₆), and mixtures thereof.--

--26. The method according to claim 22, wherein said cleaning gas is a gas containing
at least one of fluorine (F₂), chlorine (Cl₂), nitrogen trifluoride (NF₃), carbon tetrafluoride
(CF₄), hexafluoroethane (C₂F₆), octafluoropropane (C₃F₈), carbon tetrachloride (CCl₄),
pentafluorochloroethane (C₂ClF₅), trifluorochlorine (ClF₃), trifluorochloromethane (CClF₃),
sulfur hexafluoride (SF₆), and mixtures thereof.--

und
--27. A method for removing a deposited film from a wall inside a chamber, said
method comprising:
providing a hot element, said hot element disposed away from said wall and said
deposited film, said hot element having at least a surface which is composed of platinum;
heating said hot element to 400° C. or higher;
supplying a cleaning gas and first contacting said hot element with said gas to thereby
activate said gas;

thereafter contacting the deposited film with said activated cleaning gas and converting said deposited film into a gaseous substance; and removing said gaseous substance from said chamber.--

--28. The method according to claim 27, wherein said chamber comprises a CVD apparatus and the method further comprises:

heating the hot element;
supplying a material gas to the chamber;
contacting the material gas with the hot element to cause decomposition and/or activation of the material gas by said hot element; and
forming the deposited film which comprises at least one element from said material gas on a substrate.--

--29. The method according to claim 27, wherein at least a part of a surface of an inner structure of said chamber is covered with platinum.--

--30. The method according to claim 28, wherein at least a part of the surface of an inner structure of said chamber is covered with platinum.--

--31. The method according to claim 27, wherein said cleaning gas is a gas containing at least one of fluorine (F₂), chlorine (Cl₂), nitrogen trifluoride (NF₃), carbon tetrafluoride (CF₄), hexafluoroethane (C₂F₆), octafluoropropane (C₃F₈), carbon tetrachloride (CCl₄), pentafluorochloroethane (C₂ClF₅), trifluorochlorine (ClF₃), trifluorochloromethane (CClF₃), and sulfur hexafluoride (SF₆), and mixtures thereof.--

--32. The method according to claim 28, wherein said cleaning gas is a gas containing at least one of fluorine (F₂), chlorine (Cl₂), nitrogen trifluoride (NF₃), carbon tetrafluoride (CF₄), hexafluoroethane (C₂F₆), octafluoropropane (C₃F₈), carbon tetrachloride (CCl₄), pentafluorochloroethane (C₂ClF₅), trifluorochlorine (ClF₃), trifluorochloromethane (CClF₃), sulfur hexafluoride (SF₆), and mixtures thereof.--